



EMI/EMS Test Result

Model Name : MUW6 series

Approved : Kenichi Tsukada

The EUT is operated with following condition during EMI/EMS test.

Input Voltage : Rated Voltage
Output Current : Rated Current
Ambient Temperature : 25°C ± 10°C

Prepared : Soichiro Kawaguchi

#	Subject	Reference standard	Test Condition	Criteria *1	Result
1	EMI	Conducted Emission	EN55011, EN55032 Class A CISPR11, CISPR32 Class A FCC Part15, FCC Part18 Class A VCCI Class A Testing circuitry Fig. 1	-	Pass
2		Radiated Emission	EN55011, EN55032 Class A CISPR11, CISPR32 Class A FCC Part15, FCC Part18 Class A VCCI Class A Testing circuitry Fig. 1	-	Pass
3	EMS	Electrostatic discharge immunity test	IEC61000-4-2 Contact Discharge : Level 2 (4kV) Air Discharge : Level 2 (4kV) Testing circuitry Fig. 1	A	Pass
4		Radiated, radio-frequency, electromagnetic field immunity test	IEC61000-4-3 10V/m : (80MHz~1GHz) 3V/m : (1.4GHz~2.0GHz) 1V/m : (2.0GHz~2.7GHz) 80% Amplitude modulated Testing circuitry Fig. 1	A	Pass
5		Electrical fast transient / Burst immunity test	IEC61000-4-4 Level 4 (4kV) Repetition Rate : 5kHz and 100kHz Testing circuitry Fig. 1	A	Pass
6		Surge immunity test	IEC61000-4-5 Line to Line : Level 4 (2kV) Testing circuitry Fig. 2	A	Pass

*1 Definition of Criteria

Criteria A : (1) No output voltage drop with control circuit failure.
(2) No protection circuit and other circuit malfunction.

Criteria B : (1) The output voltage is temporary degradation of performance.
It recovers its normal performance without operator intervention.
(2) No protection circuit and other circuit failure.

<Notes>

Power supply shall not determine the final equipment performance against EMS test. Therefore we confirmed the output voltage performance only. EMS test should be performed as a final product.

Conditions

Test : Line conduction , Radiated emission
Electrostatic discharge immunity test
Radiated, radio-frequency, electromagnetic field immunity test
Electrical fast transient / burst immunity test

Model Name : MUW6□□

○Testing circuitry

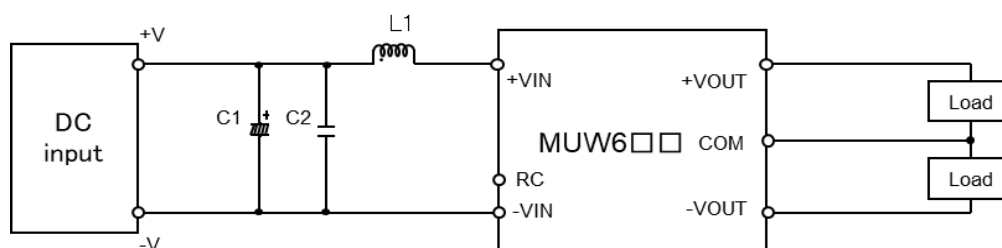


Fig.1 MUW6□□ Testing circuitry

C1 :	MUW605□	25V 1500 μ F Electric capacitor (LXZseries NIPPON CHEMI-CON)
	MUW612□	50V 100 μ F Electric capacitor (UPWseries NICHICON)
	MUW624□	—
	MUW648□	—
C2 :	MUW605□	16V 22 μ F Ceramic capacitor (GRM31CC71C226M MURATA MANUFACTURING)
	MUW612□	25V 10 μ F Ceramic capacitor (CM316X7R106K25AT KYOCERA)
	MUW624□	50V 4.7 μ F Ceramic capacitor (GRM31CR71H475K MURATA MANUFACTURING)
	MUW648□	100V 2.2 μ F Ceramic capacitor (C3216X7S2A225KT TDK)
L1 :	MUW605□	6500mA 1.5 μ H Inductor (LQH5BPN1R5N38 MURATA MANUFACTURING)
	MUW612□	5000mA 2.2 μ H Inductor (LQH5BPN2R2N38 MURATA MANUFACTURING)
	MUW624□	2600mA 10 μ H Inductor (LQH5BPN100M38 MURATA MANUFACTURING)
	MUW648□	1600mA 22 μ H Inductor (LQH5BPN220M38 MURATA MANUFACTURING)

Conditions

Test : Surge immunity test

Model Name : MUW6□□

○ Testing circuitry

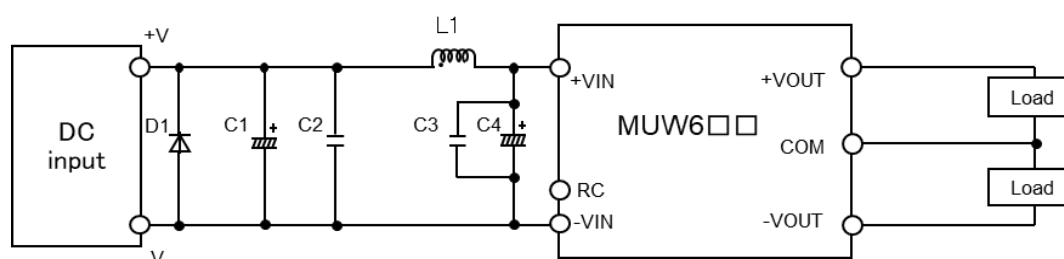


Fig.2 Testing circuitry

C1 :	MUW605□	25V 1500 μ F Electric capacitor (LXZseries NIPPON CHEMI-CON)
	MUW612□	25V 1500 μ F Electric capacitor (LXZseries NIPPON CHEMI-CON)
	MUW624□	50V 680 μ F Electric capacitor (LXZseries NIPPON CHEMI-CON)
	MUW648□	100V 680 μ F Electric capacitor (UPWseries NICHICON)
C2 :	MUW605□	16V 22 μ F Ceramic capacitor (GRM31CC71C226M MURATA MANUFACTURING)
	MUW612□	25V 10 μ F Ceramic capacitor (CM316X7R106K25AT KYOCERA)
	MUW624□	50V 4.7 μ F Ceramic capacitor (GRM31CR71H475K MURATA MANUFACTURING)
	MUW648□	100V 2.2 μ F Ceramic capacitor (C3216X7S2A225KT TDK)
C3 :	MUW605□	16V 22 μ F Ceramic capacitor (GRM31CC71C226M MURATA MANUFACTURING)
	MUW612□	25V 10 μ F Ceramic capacitor (CM316X7R106K25AT KYOCERA)
	MUW624□	50V 4.7 μ F Ceramic capacitor (GRM31CR71H475K MURATA MANUFACTURING)
	MUW648□	100V 2.2 μ F Ceramic capacitor (C3216X7S2A225KT TDK)
C4 :	MUW605□	25V 1500 μ F Electric capacitor (LXZseries NIPPON CHEMI-CON)
	MUW612□	25V 1500 μ F Electric capacitor (LXZseries NIPPON CHEMI-CON)
	MUW624□	50V 680 μ F Electric capacitor (LXZseries NIPPON CHEMI-CON)
	MUW648□	100V 680 μ F Electric capacitor (UPWseries NICHICON)
L1	MUW605□	2200mA 10 μ H Inductor(LQH5BPN100M38 MURATA MANUFACTURING)
	MUW612□	2200mA 10 μ H Inductor(LQH5BPN100M38 MURATA MANUFACTURING)
	MUW624□	1500mA 22 μ H Inductor(LQH5BPN220M38 MURATA MANUFACTURING)
	MUW648□	1100mA 47 μ H Inductor(LQH5BPN470M38 MURATA MANUFACTURING)
D1 :	MUW605□	400V 3A Diode(S3L40U SHINDENGEN)
	MUW612□	400V 3A Diode(S3L40U SHINDENGEN)
	MUW624□	400V 3A Diode(S3L40U SHINDENGEN)
	MUW648□	400V 3A Diode(S3L40U SHINDENGEN)